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(54) **SEMICONDUCTOR MEMORY**

(57) Abstract:

PROBLEM TO BE SOLVED: To provide a semiconductor memory which can be manufactured at high yield by suppressing damages on an intergate insulation layer or a tunnel insulation layer at the time of patterning, thereby reducing generation of rejectable product.

SOLUTION: A plurality of semiconductor memory elements 1 are arranged in a matrix form on a semiconductor substrate and a common word line 2, and a common bit line 3 are formed for the semiconductor memory elements in a same row. A source line 4 is formed in parallel with the bit line 3 and connected with the source region of each semiconductor memory element. Every other source contact part 6 to be connected with the source line 4 is shifted in the direction R, and the word line 2 is curved so as to detour the source contact part 6, thus constituting a semiconductor device 10.